

N-channel MOS-FET			
800V	2,3Ω	5A	50W

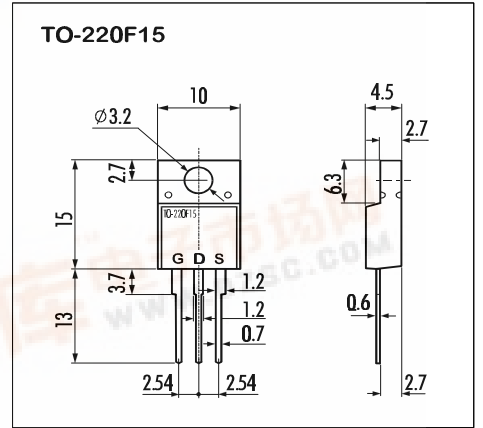
> **Features**

- High Speed Switching
- Low On-Resistance
- No Secondary Breakdown
- Low Driving Power
- High Voltage
- VGS = ± 30V Guarantee
- Avalanche Proof

> **Applications**

- Switching Regulators
- UPS
- DC-DC converters
- General Purpose Power Amplifier

> **Outline Drawing**

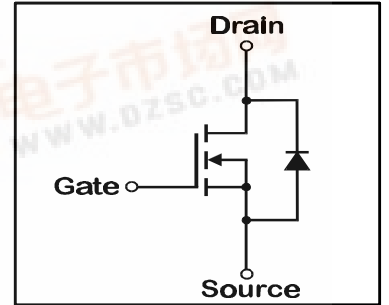


> **Maximum Ratings and Characteristics**

- Absolute Maximum Ratings (TC=25°C), unless otherwise specified

Item	Symbol	Rating	Unit
Drain-Source-Voltage	V <sub>DS</sub>	800	V
Drain-Gate-Voltage(R <sub>GS</sub> =20KΩ)	V <sub>DGR</sub>	800	V
Continous Drain Current	I <sub>D</sub>	5	A
Pulsed Drain Current	I <sub>D(puls)</sub>	20	A
Gate-Source-Voltage	V <sub>GS</sub>	±30	V
Max. Power Dissipation	P <sub>D</sub>	50	W
Operating and Storage Temperature Range	T <sub>ch</sub>	150	°C
	T <sub>stg</sub>	-55 ~ +150	°C

> **Equivalent Circuit**



- Electrical Characteristics (TC=25°C), unless otherwise specified

Item	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown-Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA V <sub>GS</sub> =0V	800			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =1mA V <sub>DS</sub> =V <sub>GS</sub>	2,5	4,0	5,0	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =800V T <sub>ch</sub> =25°C		10	500	μA
		V <sub>GS</sub> =0V T <sub>ch</sub> =125°C		0,2	1,0	mA
Gate Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±30V V <sub>DS</sub> =0V		10	100	nA
Drain Source On-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =2,5A V <sub>GS</sub> =10V		1,7	2,3	Ω
Forward Transconductance	g <sub>fs</sub>	I <sub>D</sub> =2,5A V <sub>DS</sub> =25V	1,8	3,5		S
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V		800	1200	pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> =0V		120	180	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	f=1MHz		60	90	pF
Turn-On-Time t <sub>on</sub> (t <sub>on</sub> =t <sub>d(on)</sub> +t <sub>r</sub> )	t <sub>d(on)</sub>	V <sub>CC</sub> =600V		25	40	ns
		I <sub>D</sub> =5A		100	150	ns
Turn-Off-Time t <sub>off</sub> (t <sub>off</sub> =t <sub>d(off)</sub> +t <sub>f</sub> )	t <sub>d(off)</sub>	V <sub>GS</sub> =10V		130	200	ns
		R <sub>GS</sub> =25 Ω		70	110	ns
Avalanche Capability	I <sub>AV</sub>	L=100μH T <sub>ch</sub> =25°C	5			A
Diode Forward On-Voltage	V <sub>SD</sub>	I <sub>F</sub> =2I <sub>DR</sub> V <sub>GS</sub> =0V T <sub>ch</sub> =25°C		1,0	1,5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =I <sub>DR</sub> V <sub>GS</sub> =0V		700		ns
Reverse Recovery Charge	Q <sub>rr</sub>	-dI <sub>F</sub> /dt=100A/μs T <sub>ch</sub> =25°C		15,0		μC

- Thermal Characteristics

Item	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Thermal Resistance	R <sub>th(ch-a)</sub>	channel to air			62,5	°C/W
	R <sub>th(ch-c)</sub>	channel to case			2,5	°C/W

# N-channel MOS-FET

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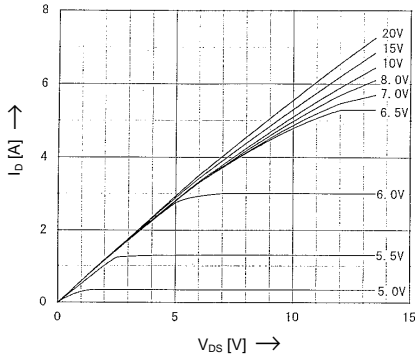
# 2SK2397-01MR

## FAP-II Series

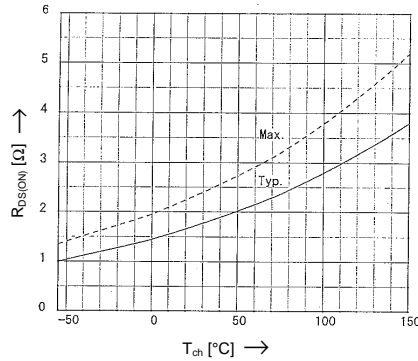


### > Characteristics

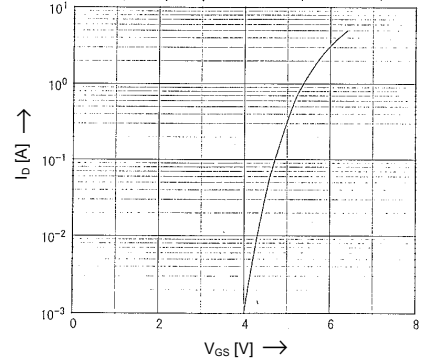
Typical Output Characteristics  
 $I_D = f(V_{DS})$ ; 80μs pulse test;  $T_{ch} = 25^\circ\text{C}$



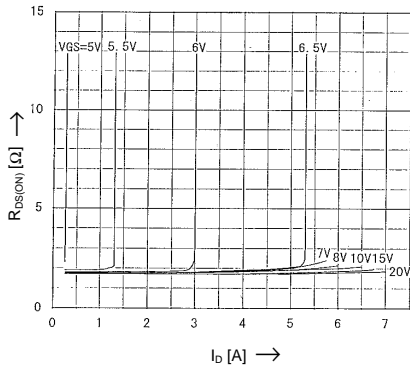
Drain-Source On-State Resistance vs.  $T_{ch}$   
 $R_{DS(on)} = f(T_{ch})$ ;  $I_D = 2.5\text{A}$ ;  $V_{GS} = 10\text{V}$



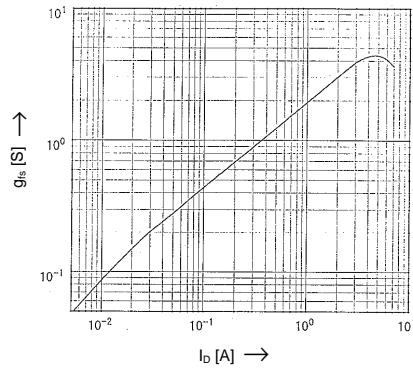
Typical Transfer Characteristics  
 $I_D = f(V_{GS})$ ; 80μs pulse test;  $V_{DS} = 25\text{V}$ ;  $T_{ch} = 25^\circ\text{C}$



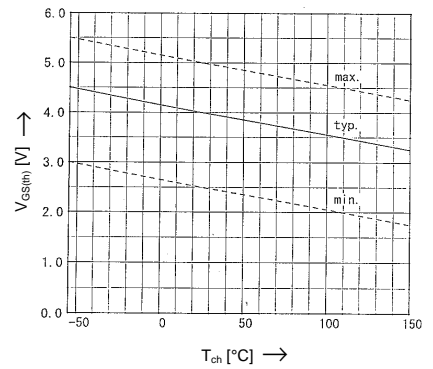
Typical Drain-Source On-State-Resistance vs.  $I_D$   
 $R_{DS(on)} = f(I_D)$ ; 80μs pulse test;  $T_{ch} = 25^\circ\text{C}$



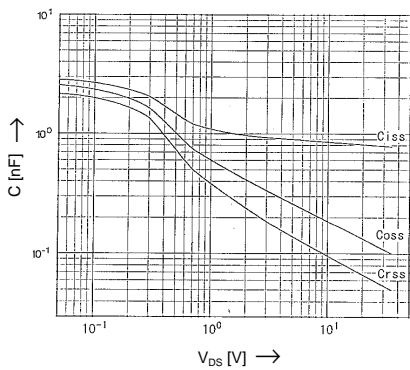
Typical Forward Transconductance vs.  $I_D$   
 $g_{fs} = f(I_D)$ ; 80μs pulse test;  $V_{DS} = 25\text{V}$ ;  $T_{ch} = 25^\circ\text{C}$



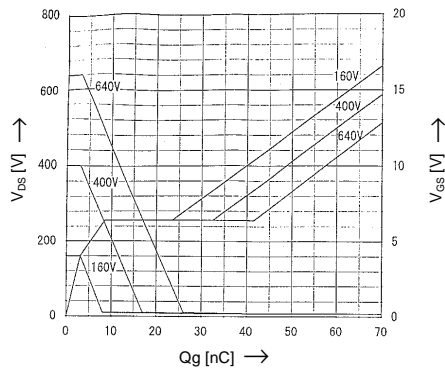
Gate Threshold Voltage vs.  $T_{ch}$   
 $V_{GS(th)} = f(T_{ch})$ ;  $I_D = 1\text{mA}$ ;  $V_{DS} = V_{GS}$



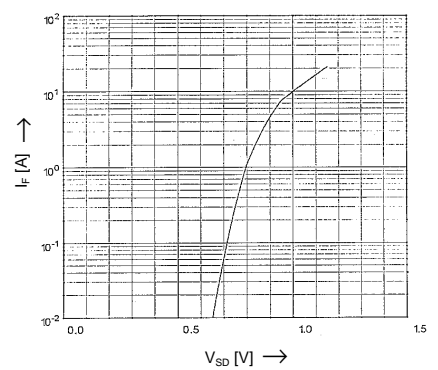
Typical Capacitances vs.  $V_{DS}$   
 $C = f(V_{DS})$ ;  $V_{GS} = 0\text{V}$ ;  $f = 1\text{MHz}$



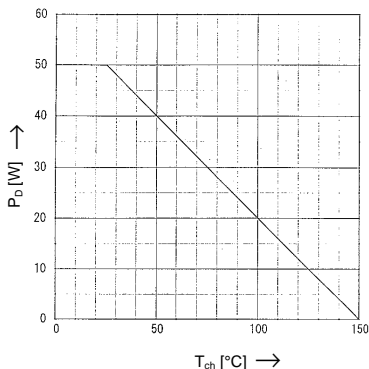
Typical Gate Charge Characteristic  
 $V_{GS} = f(Q_g)$ ;  $I_D = 5\text{A}$ ;  $T_{ch} = 25^\circ\text{C}$



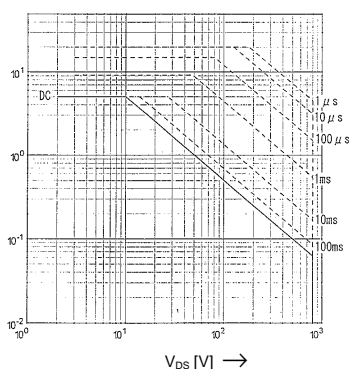
Forward Characteristics of Reverse Diode  
 $I_F = f(V_{SD})$ ; 80μs pulse test;  $V_{GS} = 0\text{V}$



Power Dissipation  
 $P_D = f(T_{ch})$



Safe Operation Area  
 $I_D = f(V_{DS})$ ;  $D = 0.01$ ;  $T_{ch} = 25^\circ\text{C}$



Transient thermal impedance

